

KSR2211

PNP EPITAXIAL SILICON TRANSISTOR

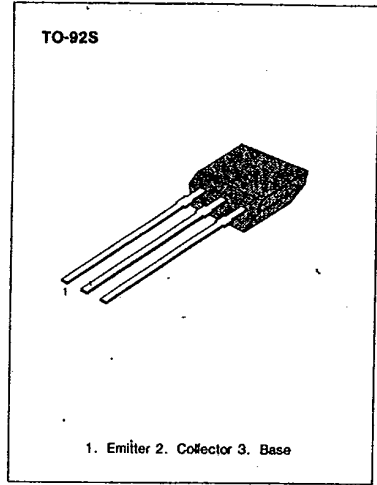
T-37-13

SWITCHING APPLICATION (Bias Resistor Built In)

- Switching Circuit, Inverter, Interface circuit
Driver circuit
- Built in bias Resistor (R=22KΩ)
- Complement to KSR1211

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

| Characteristic | Symbol | Rating | Unit |
|---------------------------|------------------|---------|------|
| Collector-Base Voltage | V _{CB0} | -40 | V |
| Collector-Emitter Voltage | V _{CEO} | -40 | V |
| Emitter-Base Voltage | V _{EB0} | -5 | V |
| Collector Current | I _c | -100 | mA |
| Collector Dissipation | P _c | 300 | mW |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature | T _{stg} | -55~150 | °C |



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ELECTRICAL CHARACTERISTICS (T_a=25°C)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|--------------------------------------|----------------------|--|-----|-----|------|------|
| Collector-Base Breakdown Voltage | BV _{CB0} | I _c =-100μA, I _E =0 | -40 | | | V |
| Collector-Emitter Breakdown Voltage | BV _{CEO} | I _E =-1mA, I _B =0 | -40 | | | V |
| Collector Cutoff Current | I _{CB0} | V _{CB} =-30V, I _E =0 | | | -0.1 | μA |
| DC Current Gain | h _{FE} | V _{CE} =-5V, I _c =-1mA | 100 | | 600 | |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | I _c =-10mA, I _B =-1mA | | | -0.3 | V |
| Output Capacitance | C _{ob} | V _{CB} =-10V, I _E =0 f=1MHz | | 5.5 | | pF |
| Current Gain-Bandwidth Product | f _T | V _{CE} =-10V, I _c =-5mA | | 200 | | MHz |
| Input Resistor | R | | 15 | 22 | 29 | KΩ |

Equivalent Circuit

